

این دیتاشیت توسط توکل الکترونیک تهیه و ارائه شده است.

جهت مشاهده قیمت، موجودی و ثبت سفارش این قطعه به وبسایت توکل الکترونیک مراجعه فرمایید.



مشاهده قیمت و خرید

برای خرید و مشاهده سایر محصولات کلیک کنید



## TOSHIBA

2SK1357

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE ( $\pi$ -MOSII·5)

# 2SK1357

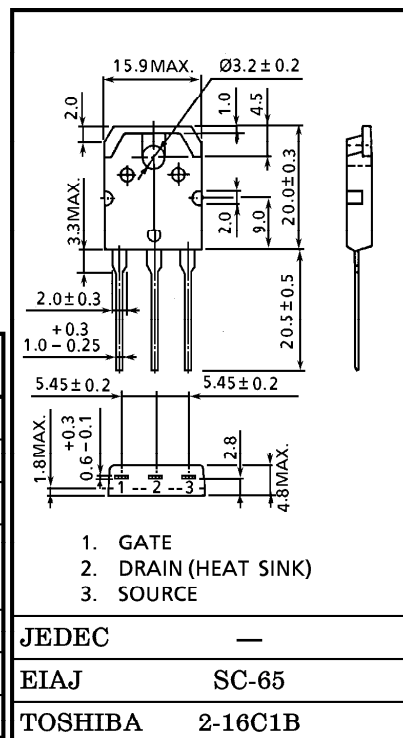
HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS.  
DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS.

INDUSTRIAL APPLICATIONS  
Unit in mm

- Low Drain-Source ON Resistance :  $R_{DS(ON)} = 2.5\Omega$  (Typ.)
- High Forward Transfer Admittance :  $|Y_{fs}| = 2.0S$  (Typ.)
- Low Leakage Current :  $I_{DSS} = 300\mu A$  (Max.) @  $V_{DS} = 720V$
- Enhancement-Mode :  $V_{th} = 1.5 \sim 3.5V$  @  $V_{DS} = 10V$ ,  $I_D = 1mA$

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

| CHARACTERISTIC                                 | SYMBOL    | RATING         | UNIT       |
|------------------------------------------------|-----------|----------------|------------|
| Drain-Source Voltage                           | $V_{DSS}$ | 900            | V          |
| Drain-Gate Voltage ( $R_{GS} = 20k\Omega$ )    | $V_{DGR}$ | 900            | V          |
| Gate-Source Voltage                            | $V_{GSS}$ | $\pm 30$       | V          |
| Drain Current                                  | DC        | $I_D$          | 5          |
|                                                | Pulse     | $I_{DP}$       | 15         |
| Drain Power Dissipation ( $T_c = 25^\circ C$ ) | $P_D$     | 125            | W          |
| Channel Temperature                            | $T_{ch}$  | 150            | $^\circ C$ |
| Storage Temperature Range                      | $T_{stg}$ | $-55 \sim 150$ | $^\circ C$ |



Weight : 4.6g

### THERMAL CHARACTERISTICS

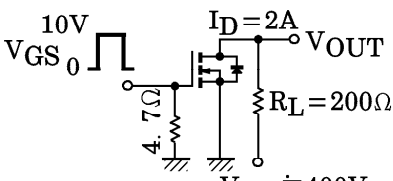
| CHARACTERISTIC                         | SYMBOL         | MAX. | UNIT           |
|----------------------------------------|----------------|------|----------------|
| Thermal Resistance, Channel to Case    | $R_{th(ch-c)}$ | 1.0  | $^\circ C / W$ |
| Thermal Resistance, Channel to Ambient | $R_{th(ch-a)}$ | 50   | $^\circ C / W$ |

THIS TRANSISTOR IS AN ELECTROSTATIC SENSITIVE DEVICE.  
PLEASE HANDLE WITH CAUTION.

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● TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

| CHARACTERISTIC                                  |               | SYMBOL         | TEST CONDITION                                                                                                                                                                                       | MIN. | TYP. | MAX.      | UNIT     |
|-------------------------------------------------|---------------|----------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------|------|-----------|----------|
| Gate Leakage Current                            |               | $I_{GSS}$      | $V_{GS} = \pm 25V, V_{DS} = 0V$                                                                                                                                                                      | —    | —    | $\pm 100$ | nA       |
| Drain Cut-off Current                           |               | $I_{DSS}$      | $V_{DS} = 720V, V_{GS} = 0V$                                                                                                                                                                         | —    | —    | 300       | $\mu A$  |
| Drain-Source Breakdown Voltage                  |               | $V_{(BR) DSS}$ | $I_D = 10mA, V_{GS} = 0V$                                                                                                                                                                            | 900  | —    | —         | V        |
| Gate Threshold Voltage                          |               | $V_{th}$       | $V_{DS} = 10V, I_D = 1mA$                                                                                                                                                                            | 1.5  | —    | 3.5       | V        |
| Drain-Source ON Resistance                      |               | $R_{DS(ON)}$   | $I_D = 2A, V_{GS} = 10V$                                                                                                                                                                             | —    | 2.5  | 2.8       | $\Omega$ |
| Forward Transfer Admittance                     |               | $ Y_{fs} $     | $V_{DS} = 20V, I_D = 2A$                                                                                                                                                                             | 1.0  | 2.0  | —         | S        |
| Input Capacitance                               |               | $C_{iss}$      | $V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$                                                                                                                                                                | —    | 700  | 1000      | pF       |
| Reverse Transfer Capacitance                    |               | $C_{rss}$      |                                                                                                                                                                                                      | —    | 55   | 90        |          |
| Output Capacitance                              |               | $C_{oss}$      |                                                                                                                                                                                                      | —    | 100  | 150       |          |
| Switching Time                                  | Rise Time     | $t_r$          |  <p><math>V_{IN} : t_r, t_f &lt; 5ns, V_{DD} \doteq 400V</math><br/>Duty <math>\leq 1\%, t_w = 10\mu s</math></p> | —    | 18   | 35        | ns       |
|                                                 | Turn-on Time  | $t_{on}$       |                                                                                                                                                                                                      | —    | 30   | 60        |          |
|                                                 | Fall Time     | $t_f$          |                                                                                                                                                                                                      | —    | 12   | 25        |          |
|                                                 | Turn-off Time | $t_{off}$      |                                                                                                                                                                                                      | —    | 70   | 140       |          |
| Total Gate Charge (Gate-Source Plus Gate-Drain) |               | $Q_g$          | $V_{DD} \doteq 400V, V_{GS} = 10V, I_D = 4A$                                                                                                                                                         | —    | 60   | 120       | nC       |
| Gate-Source Charge                              |               | $Q_{gs}$       |                                                                                                                                                                                                      | —    | 35   | —         |          |
| Gate-Drain ("Miller") Charge                    |               | $Q_{gd}$       |                                                                                                                                                                                                      | —    | 22   | —         |          |

## SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

| CHARACTERISTIC                   | SYMBOL    | TEST CONDITION                | MIN. | TYP. | MAX. | UNIT    |
|----------------------------------|-----------|-------------------------------|------|------|------|---------|
| Continuous Drain Reverse Current | $I_{DR}$  | —                             | —    | —    | 4    | A       |
| Pulse Drain Reverse Current      | $I_{DRP}$ | —                             | —    | —    | 12   | A       |
| Diode Forward Voltage            | $V_{DSF}$ | $I_{DR} = 4A, V_{GS} = 0V$    | —    | —    | —1.9 | V       |
| Reverse Recovery Time            | $t_{rr}$  | $I_{DR} = 4A, V_{GS} = 0V$    | —    | 1000 | —    | ns      |
| Reverse Recovered Charge         | $Q_{rr}$  | $dI_{DR} / dt = 100A / \mu s$ | —    | 0.13 | —    | $\mu C$ |

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